

Vishay Semiconductors

High Power Infrared Emitting Diode, 850 nm, Surface Emitter Technology



LINKS TO ADDITIONAL RESOURCES



DESCRIPTION

As part of the <u>SurfLightTM</u> portfolio, the VSMA1085400 is an infrared, 850 nm emitting diode. It features a double stack emitter chip for highest radiant power. The 42 mil chip size allows 1.5 A DC operation and supports pulsed currents up to 5.0 A.

FEATURES

- Package type: surface-mount
- Package form: high power SMD with lens
- Dimensions (L x W x H in mm): 3.4 x 3.4 x 2.45
- Centroid wavelength: $\lambda_{centroid} = 850 \text{ nm}$
- Angle of half intensity: $\phi = \pm 40^{\circ}$
- Designed for high drive currents: up to 1.5 A (DC) and up to 5 A (pulsed)

HALOGEN FREE GREEN

- Low thermal resistance: 6 K/W < R_{thJSP} < 9 K/W
- ESD: up to 5 kV (according to ANSI / ESDA / JEDEC[®] JS-001)
- Floor life: 168 h, MSL 3, according to J-STD-020E
- Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Driver and occupant monitoring
- Eye tracking
- Safety and security, CCTV

PRODUCT SUMMARY					
COMPONENT	I_e (mW/sr) at I_F = 1.0 A	φ (°)	λ _p (nm)	$\lambda_{\text{centroid}}$ (nm)	t _r (ns)
VSMA1085400	925	± 40	860	850	10

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VSMA1085400	Tape and reel	MOQ: 600 pcs, 600 pcs/reel	High power with lens		

Note

• MOQ: minimum order quantity

Pb-free





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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	YMBOL VALUE		
Reverse voltage		V _R	5	V	
Forward current		I _F	1.5	А	
Surge forward current	t _p = 100 μs	I _{FSM}	5	А	
Power dissipation		Pv	5.33	W	
Junction temperature		Тj	145	°C	
Ambient temperature range		T _{amb}	-40 to +125	°C	
Storage temperature range		T _{stg}	-40 to +125	°C	
Soldering temperature	According to Fig. 11, J-STD-020E	T _{sd}	260	°C	
Thermal resistance junction to solder point real ⁽¹⁾	JESD 51	R _{thJSP,real}	6 to 9	K/W	
Thermal resistance junction to ambient real	JESD 51	R _{thJA,real}	150	K/W	
ESD sensitivity	According to ANSI / ESDA / JEDEC JS-001	V _{ESD}	5	kV	

Note

⁽¹⁾ Thermal resistance junction to solder point real has been measured with the part mounted on an ideal heatsink and the optical output power has been deducted from the total electrical power dissipation



Fig. 1 - Power Dissipation Limit vs. Solder Point Temperature



Fig. 2 - Forward Current Limit vs. Solder Point Temperature



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BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 0.35 \text{ A}, t_p = 10 \text{ ms}$	VF	2.7	2.95	3.1	V
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F	2.8	3.1	3.3	V
	$I_F = 1.5 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F	2.9	3.25	3.55	V
	$I_F = 5 \text{ A}, t_p = 100 \ \mu \text{s}$	VF	3.2	3.9	4.4	V
Temperature coefficient of V_F	$I_F = 1 \text{ A}, t_p = 200 \ \mu \text{s}$		-	-2	-	mV/K
Reverse current		I _R	Not designed for reverse operation µA			μA
Radiant intensity	$I_F = 0.35 \text{ A}, t_p = 10 \text{ ms}$	le	275	350	425	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	l _e	700	925	1150	mW/sr
	I _F = 1.5 A, t _p = 100 μs	l _e	975	1350	1725	mW/sr
	$I_F = 5 \text{ A}, t_p = 100 \ \mu \text{s}$	le	2850	4100	5350	mW/sr
Radiant power -	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	фе	-	1425	-	mW
	$I_F = 1.5 \text{ A}, t_p = 100 \ \mu \text{s}$	фе	-	2100	-	mW
Temperature coefficient of $\boldsymbol{\phi}$	I _F = 1 A, t _p = 200 μs	ΤK _φ	-	-0.15	-	%/K
Angle of half intensity		φ	-	± 40	-	0
Peak wavelength	$I_F = 1 \text{ A}, t_p = 300 \ \mu \text{s}$	λρ	-	860	-	nm
Centroid wavelength	I _F = 1 A, t _p = 300 μs	$\lambda_{centroid}$	-	850	-	nm
Spectral bandwidth	I _F = 1 A, t _p = 300 μs	Δλ	-	30	-	nm
Temperature coefficient of λ_p	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	ΤΚ _{λρ}	-	0.25	-	nm/K
Rise time	I _F = 1 A	tr	-	10	-	ns
Fall time	I _F = 1 A	t _f	-	15	-	ns

BASIC CHARACTERISTICS (Tamb = 25 °C, unless otherwise specified)



Fig. 3 - Forward Current vs. Forward Voltage



Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

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Fig. 5 - Relative Radiant Intensity vs. Forward Current



Fig. 6 - Relative Radiant Power vs. Ambient Temperature



Fig. 7 - Relative Radiant Intensity vs. Wavelength



Fig. 8 - Relative Radiant Intensity vs. Angular Displacement



Fig. 9 - Max. Allowed Forward Current vs. Pulse Duration



Fig. 10 - Max. Allowed Forward Current vs. Pulse Duration

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4 For technical questions, contact: <u>emittertechsupport@vishay.com</u> Document Number: 80294

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TAPING DIMENSIONS in millimeters



Notes

- Empty component pockets sealed with top cover tape
- 7 inch reel 600 pieces per reel
- The maximum number of consecutive missing lamps is two
- In accordance with ANSI / EIA 481-1-A-1994 specifications



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PACKAGE DIMENSIONS in millimeters



Notes

- Tolerance is ± 0.10 mm (0.004") unless otherwise noted
- Specifications are subject to change without notice

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DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

Conditions: T_{amb} < 30 °C, RH < 60 %

Moisture sensitivity level 3, according to J-STD-020E

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-033D or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.



Cathode marking

Max. 260 °C

Max. 30 s

Max. 100 s

Max. ramp down 6 °C/s

Max. 2 cycles allowed

250

300

200

245 °C

Component location on pad

Max. 120 s

Max. ramp up 3 °C/s

50

100

150

Time (s)

Fig. 11 - Lead (Pb)-free (Sn) Infrared Reflow Solder Profile

According to J-STD-020E for Surface-Mount Components

SOLDER PROFILE

255 °C

240 °C

217 °C

300

250

200

150

100

50

0

0

Temperature (°C)

23192







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